

Supporting Information

Band gap engineering of few-layered MoS₂ with low concentration of S vacancies

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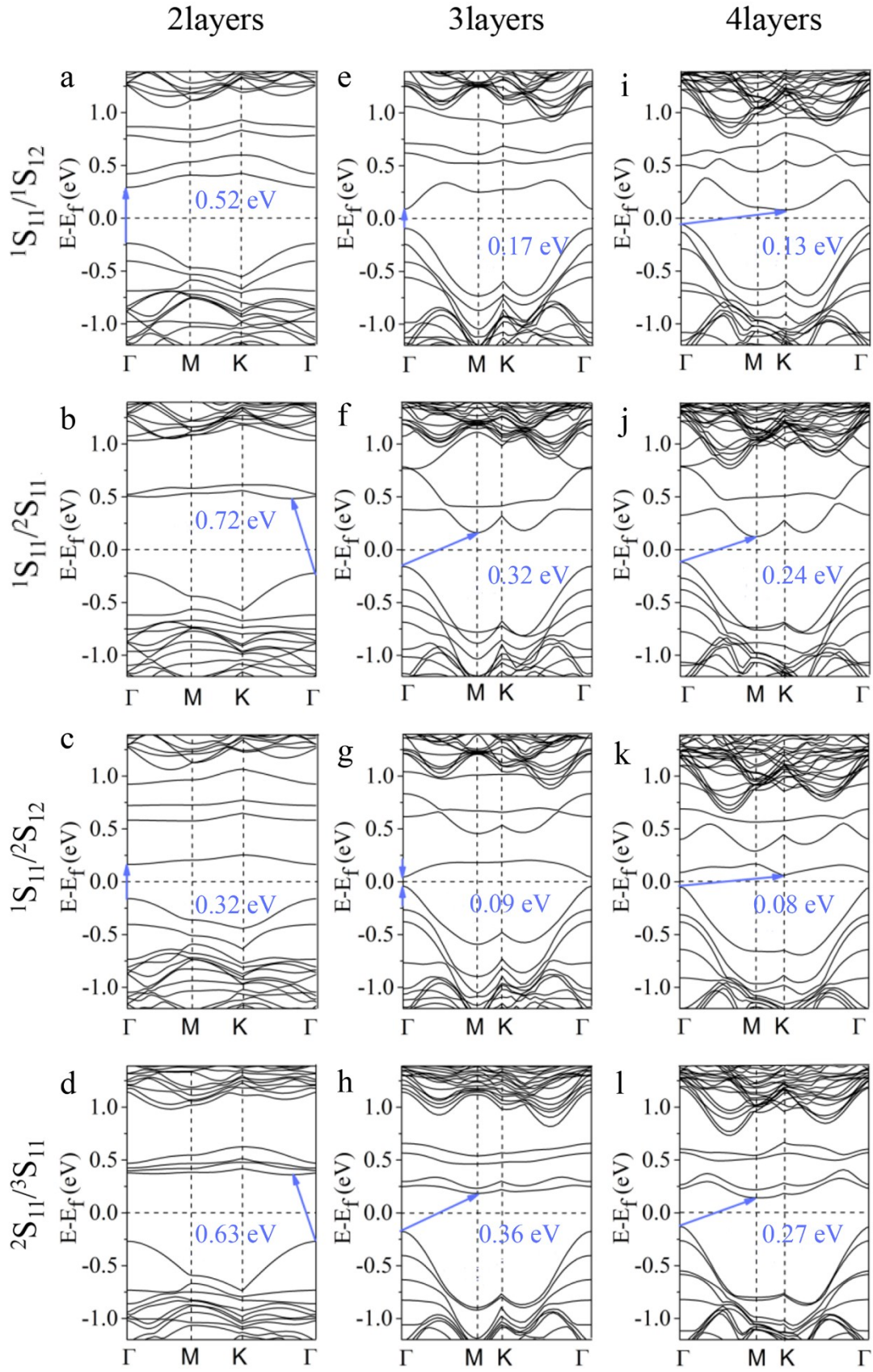


Fig.S1 Band structures for (a-d) 2-, (e-h) 3-, (i-l) 4-layered MoS₂ with $1S_{11}/1S_{12}$, $1S_{11}/2S_{11}$, $1S_{11}/2S_{12}$, $2S_{11}/3S_{11}$ combinational vacancies at 4% average concentrations.

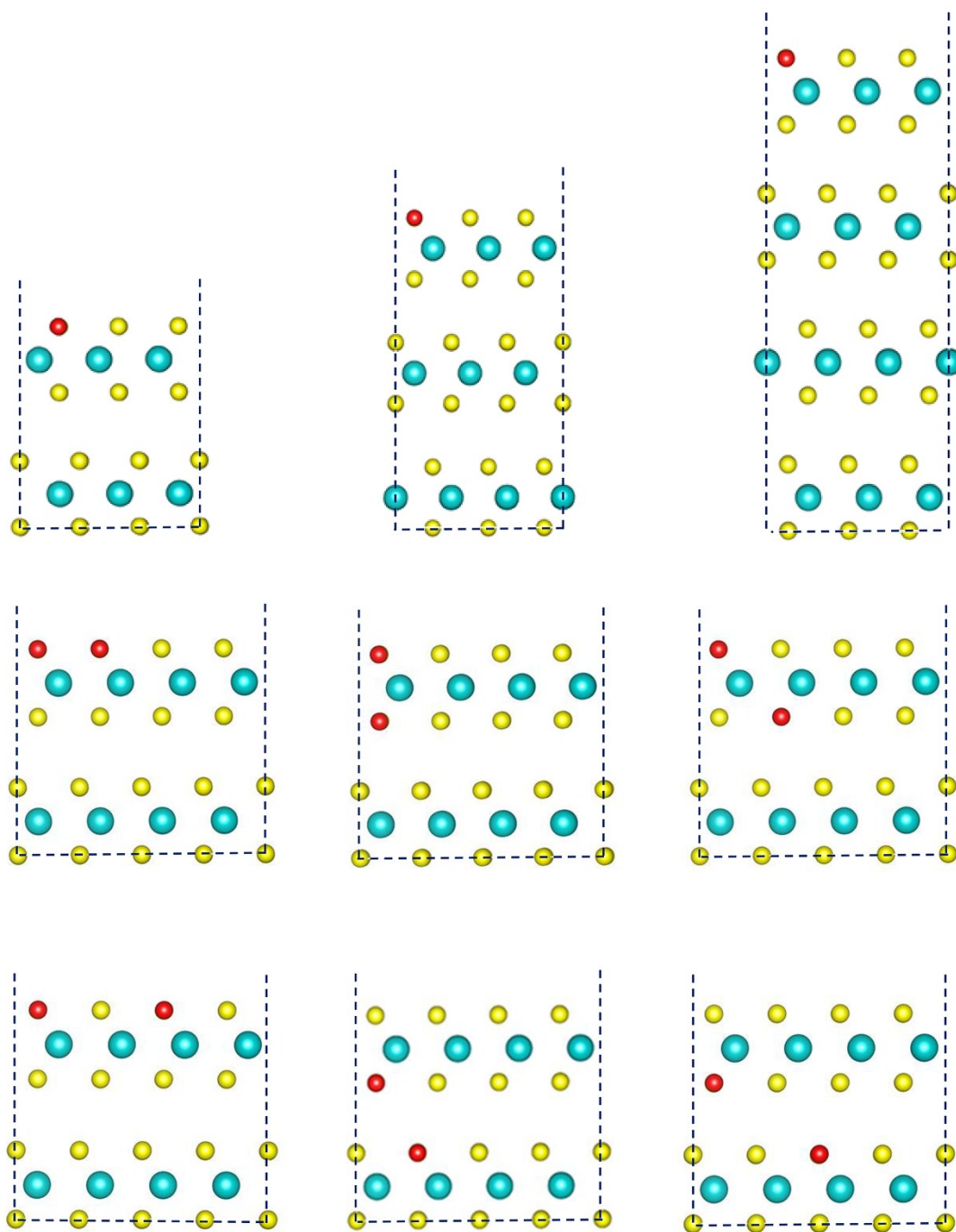


Fig.S2 The structures of MoS₂ with S vacancies (blue, yellow and red balls represent Mo, S atoms and vacancies, respectively).